CMD80R450Q/CMU80R450Q

800V, 0.39Ω typ., 11A N-Channel S uper Junction Power MOSFET

General Description

80R450Q is power MOSFET using Cmos's advanced super junction technology that can realize very low on-resistance and gate charge. It will provide much high efficiency by using optimized charge coupling technology.

Product Summary

BVDSS	$R_{DS(on)}$ max.	ID
800V	0.45Ω	11A

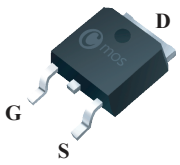
Applications

- Charger
- Adaptor
- Power Supply
- Electrodeless lamp

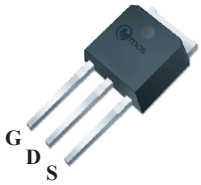
Features

- Low On-Resistance
- 100% avalanche tested
- Excellent ESD robustness
- Multi-layer Epitaxial Chip Technology
- RoHS Compliant

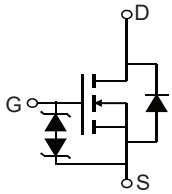
TO-252/251 Pin Configuration



TO-252
CMD80R450Q



TO-251
CMU80R450Q



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	800	V
V_{GS}	Gate-Source Voltage	±30	V
I_D@T_C=25℃	Continuous Drain Current	11	A
I_D@T_C=100℃	Continuous Drain Current	7	A
I_{DM}	Pulsed Drain Current	44	A
EAS	Single Pulse Avalanche Energy [1]	163	mJ
P_D@T_C=25℃	Total Power Dissipation	100	W
T_{STG}	Storage Temperature Range	-55 to 150	℃
T_J	Operating Junction Temperature Range	150	℃

Thermal Data

Symbol	Parameter	Rating	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient	75	℃/W
$R_{\theta JC}$	Thermal Resistance Junction-case	1.25	℃/W

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Electrical Characteristics (T_J=25℃ , unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=250uA	800	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS}=10V , I_D=7A	---	0.39	0.45	Ω
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =250uA	2.5	3.5	4.5	V
I_{DSS}	Drain-Source Leakage Current	V_{DS}=800V , V_{GS}=0V	---	---	1	uA
I_{GSS}	Gate-Source Leakage Current	V_{GS}=± 30V , V_{DS}=0V	---	---	±10	uA
gfs	Forward Transconductance	V_{DS}=20V , I_D=7A	---	9	---	S
Q_g	Total Gate Charge	I_D=11A V_{DS}=640V V_{GS}=10V	---	25	---	nC
Q_{gs}	Gate-Source Charge		---	6.9	---	
Q_{gd}	Gate-Drain Charge		---	9.3	---	
$T_{d(on)}$	Turn-On Delay Time	V_{GS}=10V V_{DD}=400V I_D=11A R_G=25Ω	---	25	---	ns
T_r	Rise Time		---	42	---	
$T_{d(off)}$	Turn-Off Delay Time		---	140	---	
T_f	Fall Time		---	22	---	
C_{iss}	Input Capacitance	V_{DS}=100V , V_{GS}=0V, f=1MHz	---	930	---	pF
C_{oss}	Output Capacitance		---	48	---	
C_{rss}	Reverse Transfer Capacitance		---	9	---	

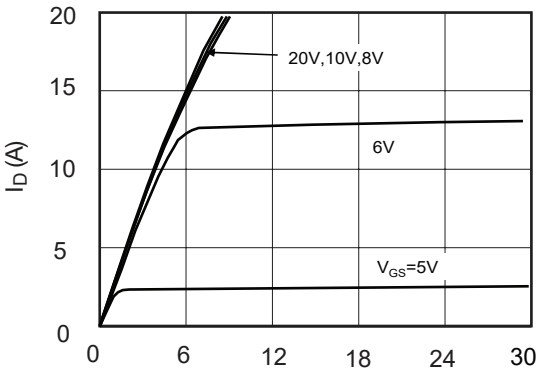
Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current	V_G=V_D=0V , Force Current	---	---	11	A
I_{SM}	Pulsed Source Current		---	---	44	A
V_{SD}	Diode Forward Voltage	V_{GS}=0V , I_S=11A ,T_J=25℃	---	0.88	1.4	V
t_{rr}	Reverse Recovery Time	di/dt = 100A/μs V_{DD}=100V , I_{SD}=11A	---	441	---	ns
Q_{rr}	Reverse Recovery Charge		---	5.4	---	μC

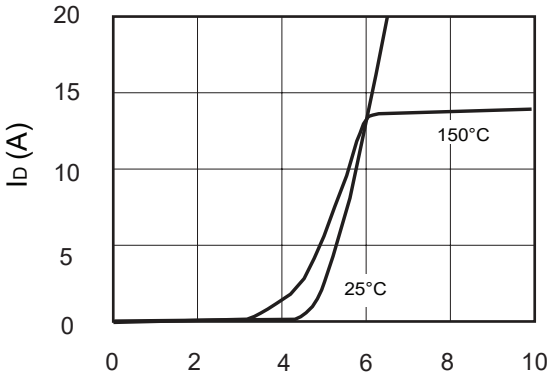
Notes:
1.The EAS data shows Max. rating . The test condition is V_{DD}=100V , V_{GS}=10V , L=30mH , I_{AS}=3.3A

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Cmos assumes no liability for customers' product design or applications.
Cmos reserver the right to improve product design ,functions and reliability wihtout notice.Please refer to the latest version of specification.

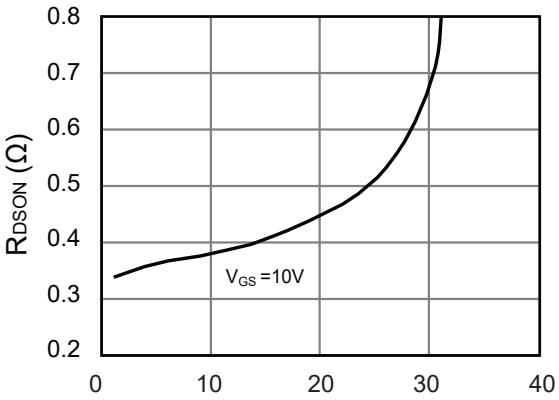
Typical Characteristics



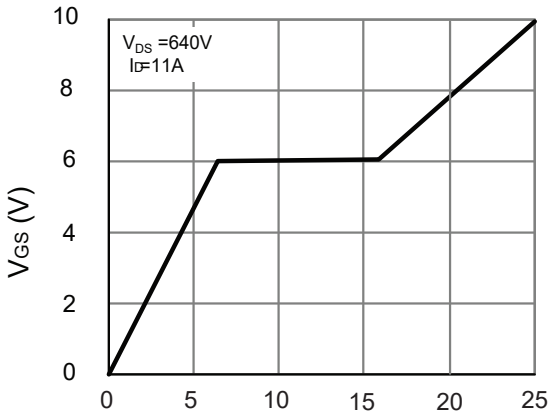
Output Characteristics



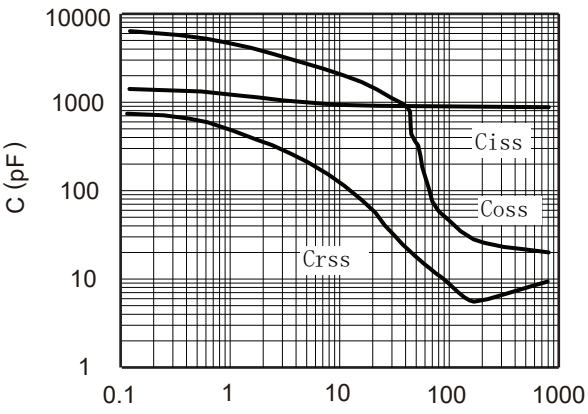
transfer characteristics



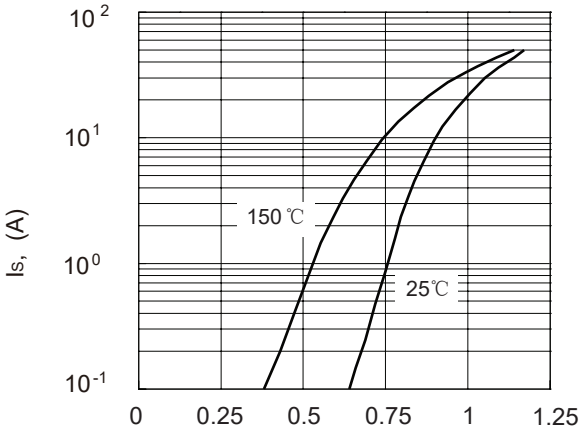
drain-source on-resistance



Gate charge vs gate-source voltage

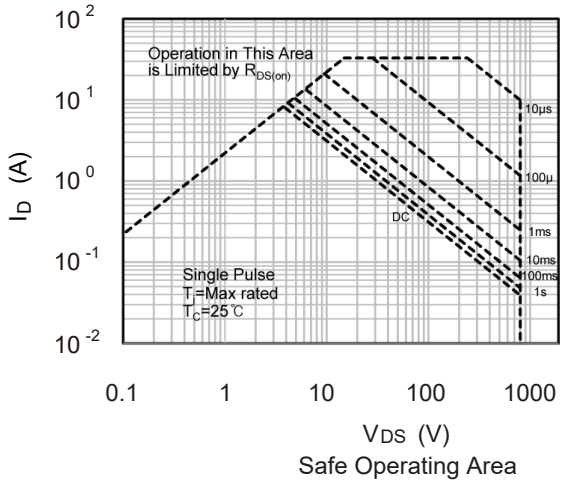


Capacitance Characteristics



Body-Diode Characteristics

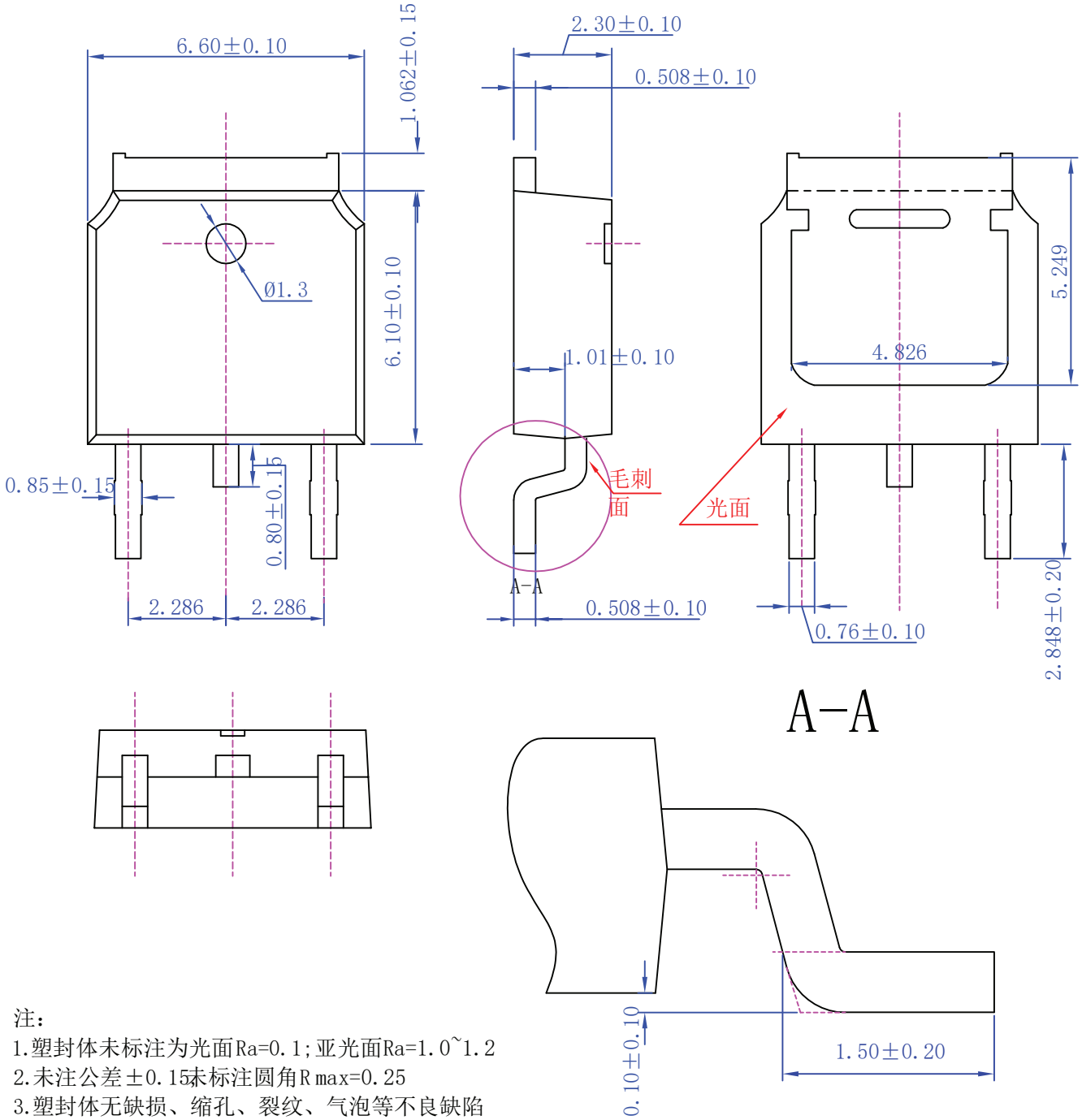
Typical Characteristics



Safe Operating Area

Package Dimension

TO-252 Unit :mm



注：

1.塑封体未标注为光面Ra=0.1;亚光面Ra=1.0~1.2

2.未注公差±0.15未标注圆角R max=0.25

3.塑封体无缺损、缩孔、裂纹、气泡等不良缺陷

4.标注单位mm

5.顶针孔不允许凸出塑封体表面

Package Dimension

TO-251A Unit :mm

